



10/723,256.

CotC

Attorney Docket

Patent

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent of

Stefan ILLEK et al.

Patent No.: 6,929,966

Issued: August 16, 2005

For: Method for Producing a Light-Emitting
Semiconductor Component

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Attn.: Certificate of Correction Branch, Commissioner for Patents, P.O. Box 1450, Arlington, VA 22313-1450, on

November 29, 2006

(Date of Deposit)

Thomas Langer

Name of applicant, assignee or Registered Representative

Signature

November 29, 2006

Date of Signature

Attn.: Certificate of Correction Branch
Commissioner for Patents
P.O. Box 1450
Arlington, VA 22313-1450

REQUEST FOR CERTIFICATE OF CORRECTION
UNDER 37 C.F.R. 1.322

SIR:

In compliance with the requirements of 37 C.F.R. 1.322, the undersigned hereby respectfully requests that the attached Certificate of Correction be issued, correcting the above-referenced Letters Patent as follows:

Claim 4, line 3, should be amended as follows:

-- treatment at a temperature in the range of 400°C[.] to --

There is no period immediately after the term "400°C", as indicated on page 13 (copy enclosed) of the original specification.

Certificate
DEC 07 2006
of Correction

DEC 08 2006

No fee is due in connection herewith. However, if any additional fees or charges are required at this time, they may be charged to our Patent and Trademark Office Deposit Account No. 03-2412.

Respectfully submitted,

COHEN, PONTANI, LIEBERMAN & PAVANE LLP

By Thomas Langer
Thomas Langer
Reg. No. 27,264
551 Fifth Avenue
New York, New York 10176
(212) 687-2770

Dated: November 29, 2006

DEC 08 2006

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO : 6,929,966
DATED : August 16, 2005
INVENTOR(S) : Stefan ILLEK et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Col. 6, line 47, replace the expression "400°C." with the following:

-- 400°C --

MAILING ADDRESS OF SENDER:

Cohen, Pontani, Lieberman & Pavane LLP
551 Fifth Avenue
Suite 1210
New York, NY 10176

PATENT NO. 6,929,966

No. of additional copies: [Click here and Type]

DEC 08 2006

WE CLAIM:

1. Method for producing a light-emitting semiconductor component having a thin-film layer sequence (14), in which a photon-emitting active zone (17) is formed, comprising:

forming the thin-film layer sequence (14) on a growth substrate;

forming a reflection contact layer (40) having contact with the thin-film layer sequence (14);

applying a diffusion barrier layer (42) to the reflection contact layer (40);

applying a solder contact layer (44) to the diffusion barrier layer (42);

subjecting the reflection contact layer (40), after it has been formed and before the diffusion barrier layer (42) is applied, to heat treatment for producing an ohmic contact; and

cleaning the surface of the reflection contact layer (40) with a first etching solution after the heat treatment.

2. Method according to Claim 1, wherein

the first etching solution is an acidic or basic solution.

3. Method according to Claim 1, wherein

the reflection contact layer (40) is cleaned with the first etching solution for a time interval in the range of 10 seconds to 10 minutes.

4. Method according to claim 1, wherein

the reflection contact layer (40) is subjected to heat treatment at a temperature in the range of 400°C to 600°C.